SONY

Diagonal 6.0mm (Type 1/3) Progressive Scan CCD Image Sensor for B/W Cameras

ICX445ALA

Description

The ICX445ALA is a diagonal 6.0mm (Type 1/3) interline CCD solid-state image sensor with a square pixel array and 1.25M effective pixels.

Progressive scan enables all pixel signals to be output separately and sequentially within 1/22.5 second. The sensitivity and smear are improved drastically through the adoption of EXview HAD CCD technology.

Features

- ◆ Supports following readout modes
 All-pixel scan mode (15 frame/s, 12.5 frame/s, 22.5 frame/s: Max.)
 Center cut-out mode (30 frame/s, 25 frame/s)
- ◆ Horizontal drive frequency: 36.0MHz, 29.0MHz
- ◆ High resolution, high sensitivity, low dark current, low smear
- Excellent anti-blooming characteristics
- ◆ No voltage adjustments (Reset gate and substrate bias need no adjustment.)
- ◆ 24-pin high precision plastic package (Dual-surface reference available)

Package

24-pin DIP (Plastic)

EXview HAD CCD_{TM}

* EXview HAD CCD is a trademark of Sony Corporation. The EXview HAD CCD is a CCD that drastically improves light efficiency by including near infrared light region as a basic structure of HAD (Hole-Accumulation Diode) sensor.

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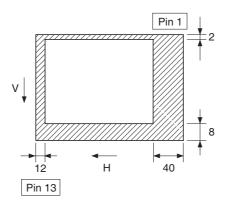
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Device Structure

- ◆ Interline CCD image sensor
- ◆ Image size Diagonal 6.0mm (Type 1/3)
- ◆ Total number of pixels 1348 (H) × 976 (V) approx. 1.32M pixels
- ♦ Number of effective pixels 1296 (H) × 966 (V) approx. 1.25M pixels
- ◆ Number of active pixels 1280 (H) × 960 (V) approx. 1.23M pixels
- ◆ Chip size 6.26mm (H) × 5.01mm (V)
- ◆ Unit cell size 3.75μm (H) × 3.75μm (V)
- ◆ Optical black Horizontal (H) direction: front 12 pixels, rear 40 pixels Vertical (V) direction: front 8 pixels, rear 2 pixels
- ◆ Number of dummy bits Horizontal (H) direction: front 4 pixels Vertical (V) direction: front 2 pixels
- Substrate material Silicon

Optical Black Position

(Top View)



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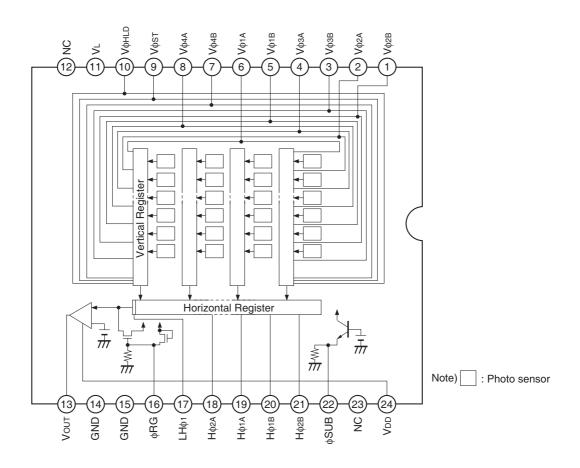
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Block Diagram and Pin Configuration



Pin Description

Pin No.	Symbol	Description	Pin No.	Symbol	Description
1	Vф2В	Vertical register transfer clock	13	Vout	Signal output
2	Vф2A	Vertical register transfer clock	14	GND	GND
3	V ф3В	Vertical register transfer clock	15	GND	GND
4	Vф3A	Vertical register transfer clock	16	φRG	Reset gate clock
5	V ф1В	Vertical register transfer clock	17	LH _{\$\psi\$1}	Horizontal register final stage transfer clock
6	Vф1A	Vertical register transfer clock	18	Нф2А	Horizontal register transfer clock
7	Vф4B	Vertical register transfer clock	19	Нф1А	Horizontal register transfer clock
8	Vф4A	Vertical register transfer clock	20	Нф1В	Horizontal register transfer clock
9	Vфsт	Horizontal addition control clock	21	Нф2В	Horizontal register transfer clock
10	Vøhld	Horizontal addition control clock	22	φSUB	Substrate clock
11	VL	Protective transistor bias	23	NC	
12	NC		24	VDD	Supply voltage

Absolute Maximum Ratings

	Ratings	Unit	Remarks			
	Vdd, Vout, фRG – фSUB	-39 to +12	V			
Against &CLID	Vφ2A, Vφ2B, Vφ3A, Vφ3B – φSUB	-46 to +17	V			
Against φSUB	Vф1A, Vф1B, Vф4A, Vф4B, VфST, VфHLD, VL – фSUB	-46 to +0.3	V			
	Ηφ1Α, Ηφ1Β, Ηφ2Α, Ηφ2Β, LΗφ1, GND – φSUB	-39 to +0.3	V			
	Vdd, Vout, фRG – GND	-0.3 to +20	V			
Against GND	Vφ1A, Vφ1B, Vφ2A, Vφ2B, Vφ3A, Vφ3B, Vφ4A, Vφ4B, VφST, VφHLD – GND	-9.0 to +17	V			
	Ηφ1Α, Ηφ1Β, Ηφ2Α, Ηφ2Β, LΗφ1 – GND	-9.0 to +4.2	V			
	Vφ2A, Vφ2B, Vφ3A, Vφ3B – VL	-0.3 to +25	V			
Against V _L	Vф1A, Vф1B, Vф4A, Vф4B, VфST, VфHLD, Нф1A, Нф1B, Нф2A, Нф2B, LНф1, GND – VL	-0.3 to +13	V			
	Potential difference between vertical clock input pins	to +13	V	*1		
Between input clock pins	Ηφ1Α, Ηφ1Β – Ηφ2Α, Ηφ2Β	-5 to +5	V			
5.55 p6	Ηφ1Α, Ηφ1Β, Ηφ2Α, Ηφ2Β – Vφ4Β, VφHLD	-13 to +13	V			
Storage temperatu	orage temperature -30 to +80 °C					
Operating tempera	ature	-10 to +60	°C			

 $^{^{*1}}$ Guaranteed up to 25V when the clock width < 10 μs and the clock duty factor < 0.1%.

Bias Conditions

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply voltage VDD		14.55	15.0	15.45	V	
Protective transistor bias	VL		*1	V		
Substrate clock	φSUB		*2			
Reset gate clock	φRG		*2			

^{*1} For the VL setting, use the VvL voltage of the vertical clock waveform or the same voltage as the VL power supply of the V driver.

DC Characteristics

Item	Symbol	Min.	Тур.	Max.	Unit	Remarks
Supply current	IDD		10.0		mA	

^{*2} Do not apply a DC bias to the substrate clock and reset gate clock pins, because a DC bias is generated internally.



Clock Voltage Conditions

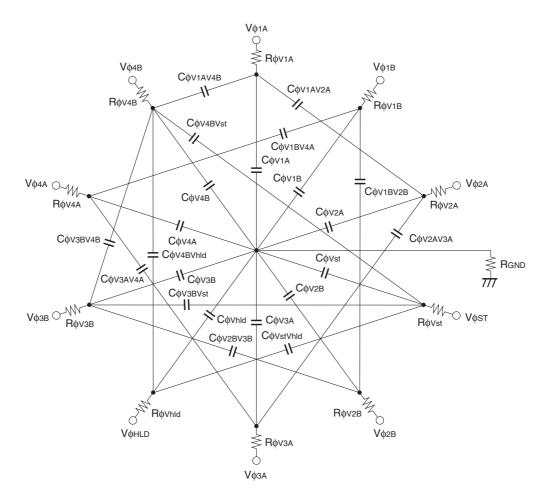
Item	Symbol	Min.	Тур.	Max.	Unit	Waveform diagram	Remarks
Readout clock voltage	Vvт	14.55	15.0	15.45	٧	1	
	VvH2, VvH3	-0.05	0	0.05	V	2	VvH = (VvH2 + VvH3)/2
	VVH1, VVH4, VVHSTR, VVHHLD	-0.2	0	0.05	V	2	
	VVL1, VVL2, VVL3, VVL4, VVLSTR, VVLHLD	-8.8	-8.5	-8.2	٧	2	V _V L = (V _V L1 + V _V L4)/2
Vertical transfer clock voltage	Vφv	8.0	8.5	8.85	V	2	$V\phi V = VVHN - VVLN$ (n = 1 to 4)
	VvH1 – VvH	-0.25		0.1	V	2	
	VvH4 – VvH	-0.25		0.1	V	2	
	Vvнн			0.5	V	2	High-level coupling
	VvhL			0.5	V	2	High-level coupling
	VVLH			0.5	V	2	Low-level coupling
	VVLL			0.5	V	2	Low-level coupling
	Vфн	3.4	3.6	3.8	V	3	
Horizontal transfer clock voltage	VHL	-0.05	0	0.05	V	3	
	Vcr	Vфн/2			V	3	Cross-point voltage
Reset gate clock voltage	Vþrg	3.4	3.6	3.8	V	4	
	VRGLH – VRGLL			0.4	V	4	Low-level coupling
	VRGL - VRGLm			0.5	V	4	Low-level coupling
Substrate clock voltage	Vфsuв	22.5	23.5	24.5	V	5	



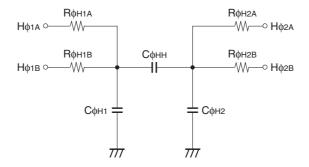
Clock Equivalent Circuit Constants

Capacitance between vertical transfer clock and GND Cφν1Α, Cφν1Β 1200 pF Cφν2Α, Cφν2B 2700 pF Cφν3Α, Cφν3B 680 pF Cφν3Α, Cφν4B 1800 pF Cφν3Α, Cφν4B 1800 pF Cφν3Α, Cφν4B 1800 pF Cφν3Α, Cφν4B 1 pF Cφν3Α, Cφν4B 1 pF Cφν3Α, Cφν4B 1 pF Cφν4Α, Cφν4B 1 pF Cφν4Α, Cφν4B 1 pF Cφν4Α, Cφν4B 1 pF Cφν1Αν2Α, Cφν4Bν2B 220 pF Cφν1Αν2Α, Cφν1Βν2Α 47 pF Cφν2Αν3Α, Cφν2Βν3B 220 pF Cφν2Αν3Α, Cφν2Βν3B 220 pF Cφν2Αν3Α, Cφν2Βν3B 390 pF Cφν3Βν3t, Cφν3Βν3t, Cφν3Εν3t,
Capacitance between vertical transfer clock and GND Сфvза, Сфvзв 680 pF Сфvза, Сфvзв 1800 pF Сфvза, Сфvзв 1800 pF Сфvза, Сфvзв 1 pF Сфvза, Сфvзв 220 pF Сфvзвизв 220 pF Сфvзвизв, Сфvзвизв 220 pF Сфvзвизв 390 pF Сфvзвизв, Сфизвизв, Сфизвиз
and GND Cφν3Α, Cφν3Β 680 pF Cφν4Α, Cφν4B 1800 pF Cφνst, Cφνhid 1 pF Cφν1Αν2Α, Cφν1Βν2B 220 pF Cφν1Αν2Α, Cφν1Βν2B 47 pF Cφν1Αν2Α, Cφν1Βν3Α 220 pF Cφν2Αν3Α, Cφν2Βν3Β 220 pF Cφν2Αν3Α, Cφν2Βν3Β 390 pF Cφν3Βν4Α, Cφν3Βν4Α, Cφν3Βν4Βν1α 47 pF Cφν3Βν4Βν1α 47 pF Cφν3Βν4Βν1α 47 pF Cφν3Βντι, Cφν4Βντι, Cφν1νη Δη 47 pF Cαρασίταιας between horizontal transfer clock and GND CφH1 32 pF Cαρασίταιας between reset gate clock and GND CφH2 30 pF Cαρασίταιας between horizontal final stage transfer clock and GND CφSUB 330 pF Cαρασίταιας between horizontal final stage transfer clock and GND CφLH1 1 pF
Cφν4A, Cφν4B 1800 pF Cφνst, Cφνhid 1 pF Cφν1Aν2A, Cφν1Bν2B 220 pF Cφν1Aν2A, Cφν1Bν2B 47 pF Cφν1Aν4B, Cφν1Bν4A 47 pF Cφν2Aν3A, Cφν2Bν3B 220 pF Cφν2Bν3B 390 pF Cφν3Bν4B 390 pF Cφν3Bν4B 47 pF Cφν3Bν4B 47 pF Cφν4Bνthid 47 pF Cφν4Bνst, Cφν4Bνthid 47 pF Cφν4Bνst, Cφν4Bνthid 47 pF Cφν4Bνst, Cφν4Bνthid 47 pF Cφν4Bνst, Cφν4Bνthid 47 pF Cφν4Bνthid 56
Cφν1Αν2Α, Cφν1Βν2Β 220 pF Cφν1Βν2Β 47 pF Cφν1Βν2Α 47 pF Cφν1Βν4Α 47 pF Cφν2Αν3Α, Cφν2Βν3Β 220 pF Cφν2Αν3Α, Cφν2Βν3Β 390 pF Cφν3Βν4Α, Cφν3Βν4Β, Cφν3Βν4Β, Cφν3Βν4Β, Cφν3Βν4Β, Cφν3Βν4Β, Cφν3Βν4Β, Cφν3Βν4Β, Cφν4Βν1Π 47 pF Cαρασίταια between horizontal transfer clock and GND CφH1 32 pF Cαρασίταια between horizontal transfer clocks CφHH 56 pF Cαρασίταια between reset gate clock and GND CφRG 1 pF Cαρασίταια between substrate clock and GND CφSUB 330 pF Cαρασίταια between horizontal final stage transfer clock and GND CφLH1 1 pF Rφν1Α, Rφν1Β, Rφν1Α, Rφν1Β, PF PF
Cφν18ν2B 220 pF Cφν1Αν4B, Cφν18ν4A 47 pF Cφν2Αν3A, Cφν2Βν3B 220 pF Cφν2Αν3A, Cφν2Βν3B 390 pF Cφν3Αν4A, Cφν3Βν4B 390 pF Cφν3Βν4B, Cφν3Βν4B, Cφν3Βν4B, Cφν3Βν4B 47 pF Cφν3Βν4B, Cφν4Βν4Id 47 pF Cφν4Βν4B, Cφν4Βν4Id 47 pF Cαpacitance between horizontal transfer clock and GND CφH1 32 pF Cαpacitance between horizontal transfer clocks CφH1 32 pF Cαpacitance between horizontal transfer clocks CφHH 56 pF Cαpacitance between reset gate clock and GND CφRG 1 pF Cαpacitance between horizontal final stage transfer clock and GND CφLH1 1 pF Rφν1A, Rφν1B, Rφν1A, Rφν1B, PF
C φν18ν4Α 47 pF Cφν2Αν3Α, Cφν2Αν3Α, Cφν2Βν3Β 220 pF Cφν2Αν3Α, Cφν2Βν3Β 390 pF Cφν3Αν4Α, Cφν3Αν4Α, Cφν3Βν4Β 390 pF Cφν3Βν3Ε, Cφν3Βν4Ε, Cφν3Βν4Ε, Cφν3Εν1Η 47 pF Cαρασίταιce between horizontal transfer clock and GND CφH1 32 pF Cαρασίταιce between horizontal transfer clocks CφH1 32 pF Cαρασίταιce between horizontal transfer clocks CφHH 56 pF Cαρασίταιce between reset gate clock and GND CφRG 1 pF Cαρασίταιce between horizontal final stage transfer clock and GND CφLH1 1 pF Rφν1Α, Rφν1Β, PF
Capacitance between vertical transfer clocks Cφν28ν3B 220 pF Cφν3Αν4A, Cφν3Βν4B 390 pF Cφν3Βν4B 47 pF Cφν4Βνhld 47 pF Capacitance between horizontal transfer clock and GND CφH1 32 pF Capacitance between horizontal transfer clocks CφH1 32 pF Capacitance between horizontal transfer clocks CφH4 56 pF Capacitance between reset gate clock and GND CφRG 1 pF Capacitance between substrate clock and GND CφSUB 330 pF Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF Rφν1A, Rφν1B, Rφν1A, Rφν1B, 1 pF
Сфv3av4A, Сфv3bv4B 390 pF Сфv3bvst, Сфv4bvhld 47 pF Сфv4bvst, Сфvstvhld 47 pF Сарасitance between horizontal transfer clock and GND Сфн1 32 pF Сарасitance between horizontal transfer clocks Сфн2 30 pF Сарасitance between horizontal transfer clocks Сфнн 56 pF Сарасitance between reset gate clock and GND Сфкв 1 pF Сарасitance between substrate clock and GND Сфsub 330 pF Сарасitance between horizontal final stage transfer clock and GND Сфsub 330 pF СфLH1 1 pF Кфv1A, Rфv1B, 1 pF
Cφν48νhid 47 pF Cφν48νst, Cφνstvhid 47 pF Capacitance between horizontal transfer clock and GND CφH1 32 pF Capacitance between horizontal transfer clocks CφH2 30 pF Capacitance between reset gate clock and GND CφHH 56 pF Capacitance between reset gate clock and GND CφRG 1 pF Capacitance between substrate clock and GND CφsuB 330 pF Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF Rφv1A, Rφv1B, Rφv1A, Rφv1B, 1 pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$
Capacitance between horizontal transfer clocks CφH2 30 pF Capacitance between horizontal transfer clocks CφHH 56 pF Capacitance between reset gate clock and GND CφRG 1 pF Capacitance between substrate clock and GND CφSUB 330 pF Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF RφV1A, RφV1B, RφV1A, RφV1B, RφV1B, RφV1B,
Сарасitance between horizontal transfer clocks Сфнн 56 pF Capacitance between reset gate clock and GND СфRG 1 pF Capacitance between substrate clock and GND Сфsub 330 pF Capacitance between horizontal final stage transfer clock and GND CфLH1 1 pF Rфv1A, Rфv1B,
Capacitance between reset gate clock and GND CφRG 1 pF Capacitance between substrate clock and GND CφSUB 330 pF Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF RφV1A, RφV1B, RφV1A, RφV1B, RφV1A, RφV1B, RφV1A, RφV1B,
Capacitance between substrate clock and GND Cφsub 330 pF Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF Rφv1A, Rφv1B, Rφv1A, Rφv1B, The control of
Capacitance between horizontal final stage transfer clock and GND CφLH1 1 pF RφV1A, RφV1B,
transfer clock and GND Collin Collin
Vertical transfer clock series resistance Rφνst, Rφνhld
Rφν2A, Rφν2B, 82 Rφν3A, Rφν3B 82
Vertical transfer clock ground resistance R _{GND} 15 Ω
Horizontal transfer clock series resistance RφH1A, RφH1B 18 Ω
Rhonzontal transfer clock series resistance $Rhonzontal Rhonzontal transfer clock series resistance Rhonzontal Rhonzontal Rhonzontal transfer clock series resistance Rhonzontal Rho$
Substrate clock series resistance R ϕ SUB 300 k Ω

SONY ICX445ALA



Vertical transfer clock equivalent circuit

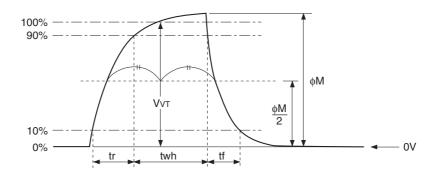


Horizontal transfer clock equivalent circuit

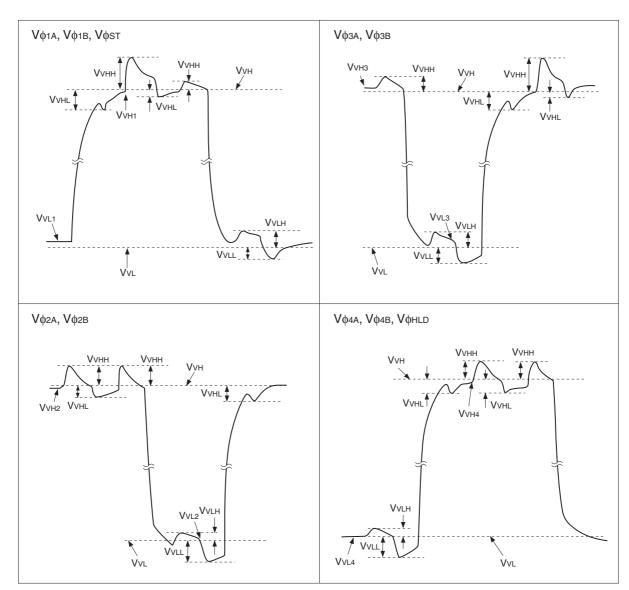


Drive Clock Waveform Conditions

1. Readout clock waveform



2. Vertical transfer clock waveform



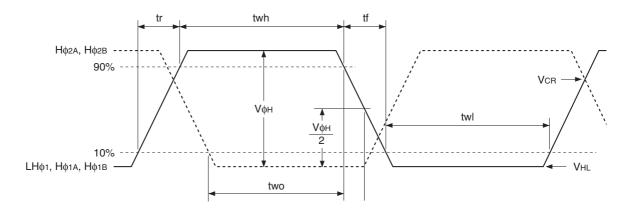
 $V_{VH} = (V_{VH2} + V_{VH3})/2$

 $V_{VL} = (V_{VL1} + V_{VL4})/2$

 $V\phi V = VVHN - VVLN (n = 1 to 4)$



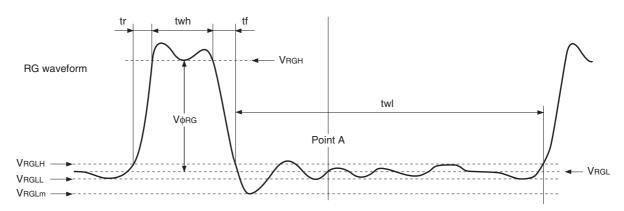
3. Horizontal transfer clock waveform



VCR is the cross-point voltage of the horizontal transfer clocks $H\phi_{1A}$, $H\phi_{1B}$, $LH\phi_{1}$ and $H\phi_{2A}$, $H\phi_{2B}$ waveforms that is on the $H\phi_{1A}$, $H\phi_{1B}$, $LH\phi_{1}$ rise side.

"two" is the overlapped period with twh and twl of the horizontal transfer clocks Hφ1A, Hφ1B, LHφ1 and Hφ2A, Hφ2B.

4. Reset gate clock waveform



VRGLH is the maximum value and VRGLL is the minimum value of the coupling waveform during the period from Point A in the above diagram until the rising edge of RG.

In addition, VRGL is the average value of VRGLH and VRGLL.

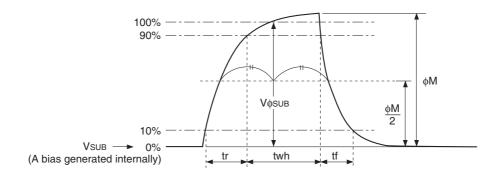
VRGL = (VRGLH + VRGLL)/2

Assuming VRGH is the minimum value during the interval twh, then;

 $V \phi RG = V RGH - V RGL$

VRGLm is the negative overshoot level during the falling edge of RG.

5. Substrate clock waveform





Clock Switching Characteristics

(Horizontal drive frequency: 36.0MHz)

Item	Symbol	twh			twl		tr		tf			Unit	Remarks		
item	Symbol	Min.	Тур.	Мах.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Мах.	Offic	Nemarks
Readout clock	VT	1.52	1.72						0.5			0.5		μS	During readout
Vertical transfer clock	Vф1A, Vф1B, Vф2A, Vф2B, Vф3A, Vф3B, Vф4A, Vф4B, VфST, VфHLD										15		250	ns	When using CXD3400N
Horizontal transfer clock	LHφ1, Hφ1A, Hφ1B	8	9		8	9			5	6		5	6	ns	When driving at 3.6V during imaging, tf ≥ tr – 2ns
	Нф2А, Нф2В	8	9		8	9			5	6		5	6	2	
Reset gate clock	φRG	4	5.5			17.2			2			3		ns	
Substrate clock	φSUB	0.9	1.8							0.25			0.25	μS	When draining charge

Item	Symbol		two		Unit	Remarks	
item	Symbol	Min.	Тур.	Мах.	Offic	Remains	
Horizontal transfer clock	LHφ1, Hφ1A, Hφ1B, Hφ2A, Hφ2B	8	9		ns		

Spectral Sensitivity Characteristics

(excludes lens characteristics and light source characteristics)

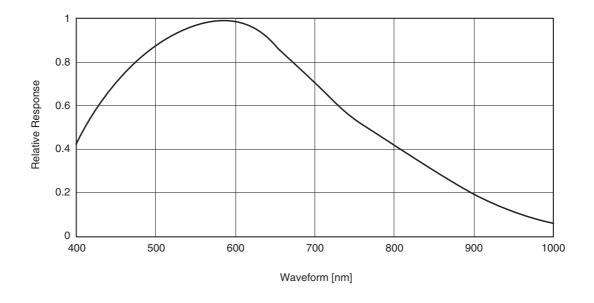


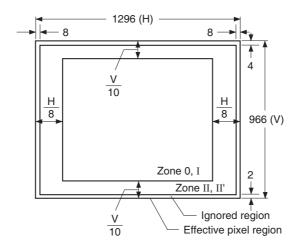
Image Sensor Characteristics (Center cut-out drive, 30 frame/s)

(Ta = 25°C)

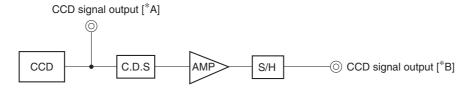
Item	Symbol	Min.	Тур.	Max.	Unit	Measurement method	Remarks
Sensitivity 1	S1	300	380		mV	1	1/30s accumulation
Sensitivity 2	S2	1000	1500		mV	2	1/30s accumulation
Saturation signal	Vsat	350			mV	3	Ta = 60°C
Smear	Sm		-104	-96	dB	4	
Video signal shading	SH			20	%	5	Zone 0 and I
Video signal shading	311			25	%	5	Zone 0 to II'
Dark signal	Vdt			2	mV	6	Ta = 60°C, 1/30s accumulation
Dark signal shading	ΔVdt			1	mV	7	Ta = 60°C, 1/30s accumulation*1
Lag	Lag			0.5	%	8	

^{*1} Excludes vertical dark signal shading caused by the vertical register high-speed transfer.

Zone Definition of Video Signal Shading



Measurement System



Note) Adjust the amplifier gain so that the gain between [* A] and [* B] equals 1.

Image Sensor Characteristics Measurement Method

Measurement conditions

- 1. In the following measurements, the device drive conditions are at the typical values of the bias and clock voltage conditions.
- 2. In the following measurements, spot pixels are excluded and, unless otherwise specified, the optical black (OB) level is used as the reference for the signal output, and the value measured at point [*B] of the measurement system is used.

Definition of Standard Imaging Conditions

◆ Standard imaging condition I:

Use a pattern box (luminance: 706cd/m², color temperature of 3200K halogen source) as a subject. (Pattern for evaluation is not applicable.) Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter and image at F8. The luminous intensity to the sensor receiving surface at this point is defined as the standard sensitivity testing luminous intensity.

◆ Standard imaging condition II:

This indicates the standard imaging condition I with the IR cut filter removed.

Standard imaging condition III:

Image a light source (color temperature of 3200K) with a uniformity of brightness within 2% at all angles. Use a testing standard lens with CM500S (t = 1.0mm) as an IR cut filter. The luminous intensity is adjusted to the value indicated in each testing item by the lens diaphragm.

1. Sensitivity 1

Set the measurement condition to the standard imaging condition I. After setting the electronic shutter mode with a shutter speed of 1/100s, measure the signal output (Vs1) at the center of the screen, and substitute the value into the following formula.

$$S1 = Vs1 \times (100/30) [mV]$$

2. Sensitivity 2

Set the measurement condition to the standard imaging condition II. After setting the electronic shutter mode with a shutter speed of 1/500s, measure the signal output (Vs2) at the center of the screen, and substitute the value into the following formula.

$$S2 = V_{S2} \times (500/30) [mV]$$

3. Saturation signal

Set the measurement condition to the standard imaging condition III. After adjusting the luminous intensity to 10 times the intensity with the average value of the signal output, 150mV, measure the minimum value of the signal output.

4. Smear

Set the measurement condition to the standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity to 500 times the intensity with the average value of the signal output, 150mV. When the readout clock is stopped and the charge drain is executed by the electronic shutter at the respective H blankings, measure the maximum value (VSm) of the signal output, and substitute the value into the following formula.

Sm = $20 \times log ((VSm/150) \times (1/500) \times (1/10)) [dB] (1/10V method conversion value)$

SONY ICX445ALA

5. Video signal shading

Set the measurement condition to the standard imaging condition III. With the lens diaphragm at F5.6 to F8, adjust the luminous intensity so that the average value of the signal output is 150mV. Then measure the maximum value (Vmax) and the minimum value (Vmin) of the signal output, and substitute the values into the following formula.

 $SH = (Vmax - Vmin)/150 \times 100 [\%]$

6. Dark signal

Measure the average value (Vdt) of the signal output with the device ambient temperature of 60°C and the device in the light-obstructed state, using the horizontal idle transfer level as the reference.

7. Dark signal shading

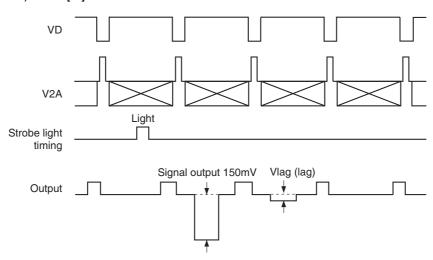
After the measurement item 6, measure the maximum value (Vdmax) and the minimum value (Vdmin) of the dark signal output, and substitute the values into the following formula.

 $\Delta Vdt = Vdmax - Vdmin [mV]$

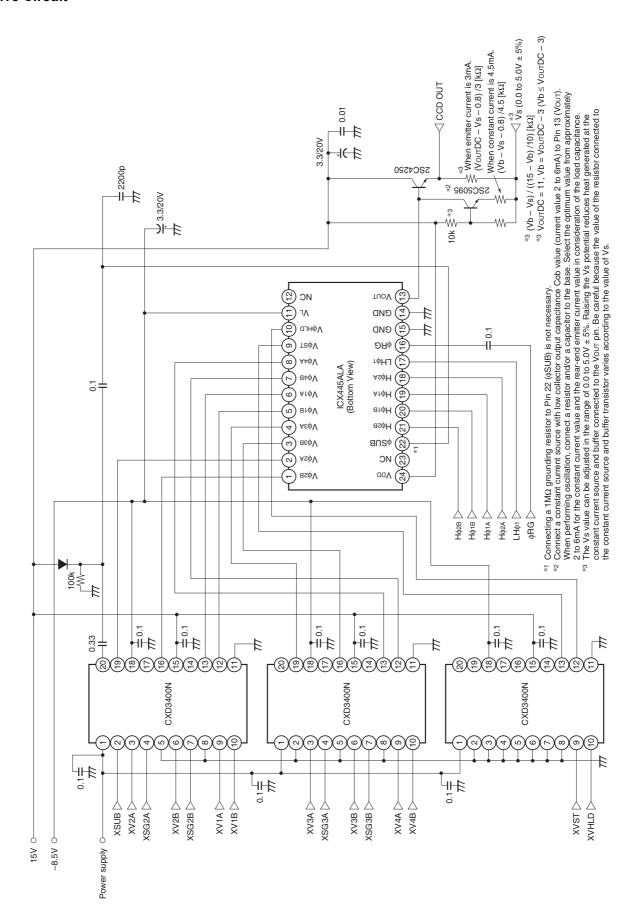
8. Lag

Adjust the signal output value generated by the strobe light to 150mV. After setting the strobe light so that it strobes with the following timing, measure the residual signal level (Vlag), and substitute the value into the following formula.

Lag = $(Vlag/150) \times 100 [\%]$

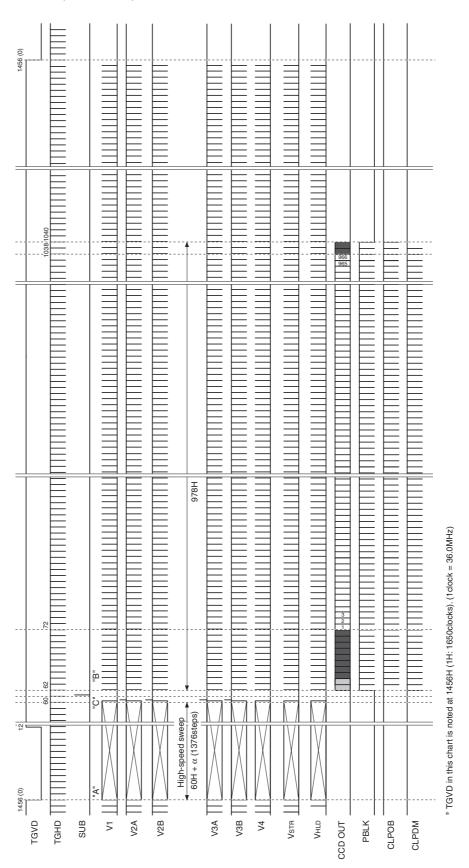


Drive Circuit



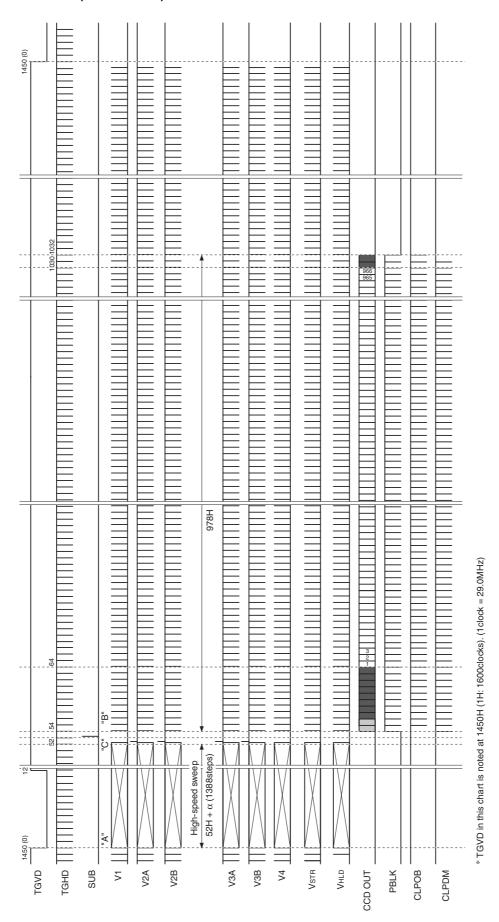
Drive Timing Chart

All-pixel Scan Mode (15 frame/s) Vertical Direction



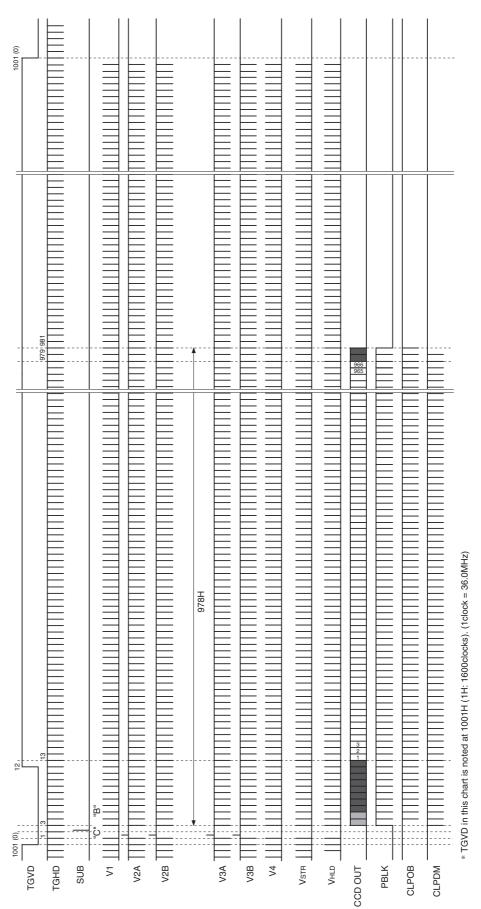


All-pixel Scan Mode (12.5 frame/s) Vertical Direction



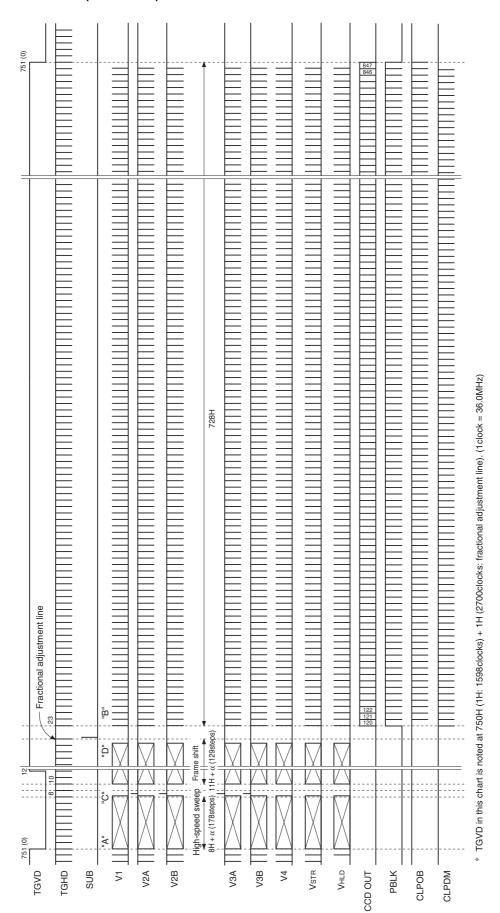


All-pixel Scan Mode (22.5 frame/s) Vertical Direction





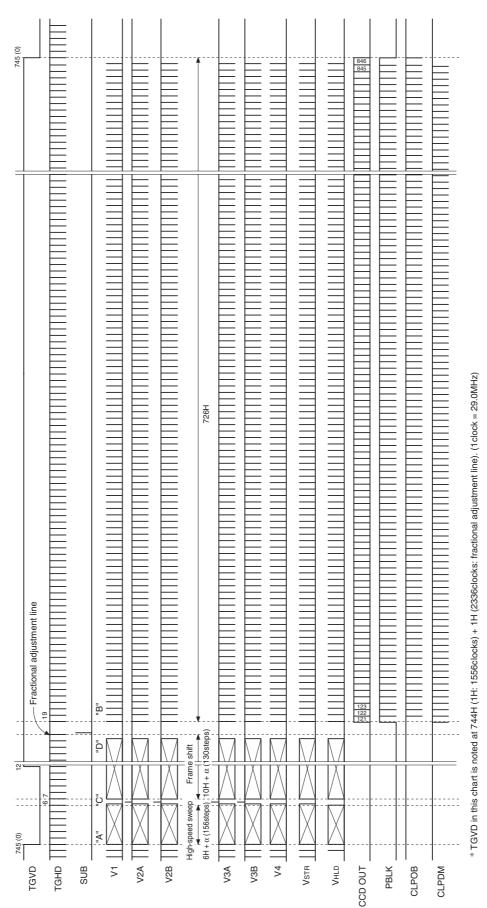
Center Cut-out Mode (30 frame/s) Vertical Direction



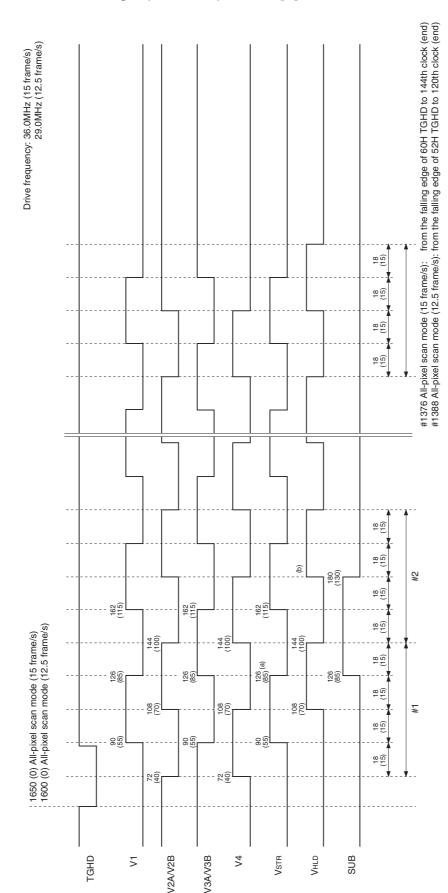
- 19 -



Center Cut-out Mode (25 frame/s) Vertical Direction



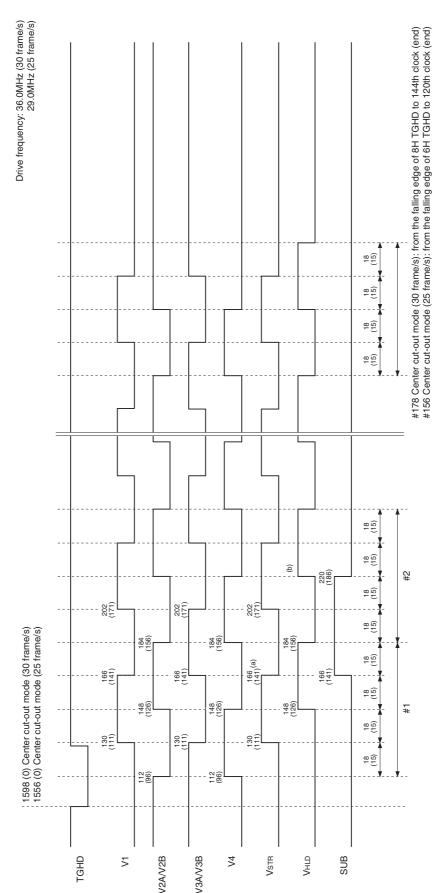
All-pixel Scan Mode (15 frame/s, 12.5 frame/s) Horizontal Direction High-speed Sweep Block [A]



* Synchronize the rising edge of SUB with the first falling edge of VSTR (a) counting from the falling edge of TGHD, and synchronize the falling edge of SUB with the first rising edge of VHLD (b) counting from (a).

The numbers at the output pulse transition points indicate the count at the rising edge of the clock from the falling edge of TGHD. The numbers on the upper level are for 36.0MHz, and the numbers in parentheses on the lower level are for 29.0MHz.

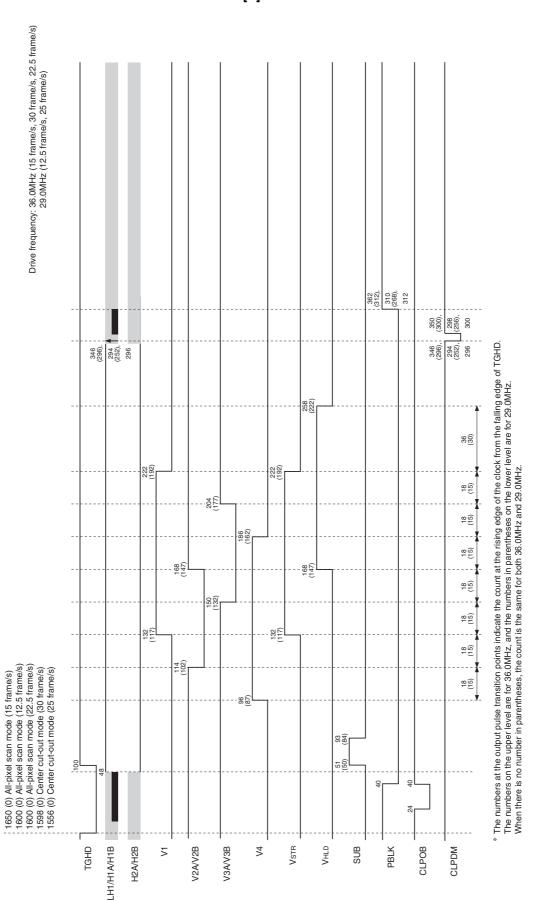
Center Cut-out Mode (30 frame/s, 25 frame/s) Horizontal Direction High-speed Sweep Block [A]



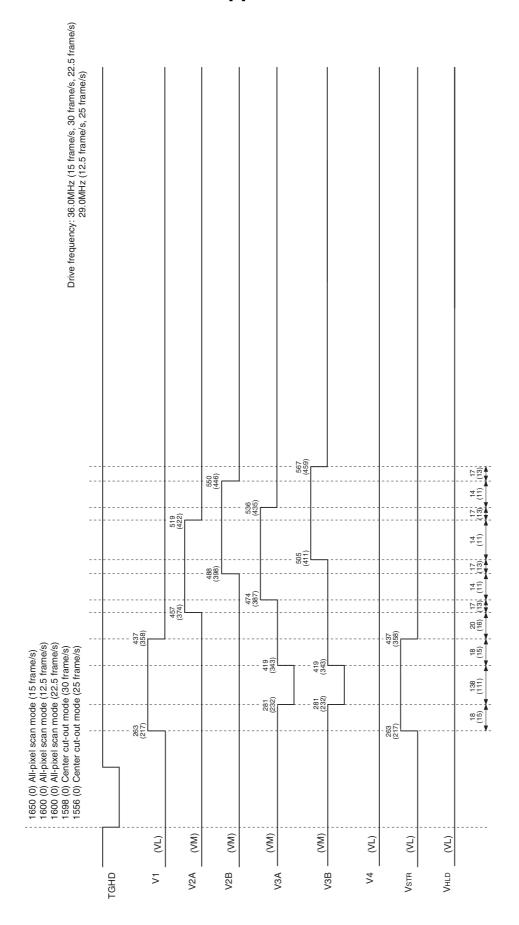
* Synchronize the rising edge of SUB with the first falling edge of VSTR (a) counting from the falling edge of TGHD, and synchronize the falling edge of SUB with the first rising edge of VHLD (b) counting from (a).

The numbers at the output pulse transition points indicate the count at the rising edge of the clock from the falling edge of TGHD. The numbers on the lower level are for 36.0MHz, and the numbers in parentheses on the lower level are for 28.0MHz.

All-pixel Scan Mode (15 frame/s, 12.5 frame/s, 22.5 frame/s)/Center Cut-out Mode (30 frame/s, 25 frame/s)
Horizontal Direction Normal Transfer Block [B]



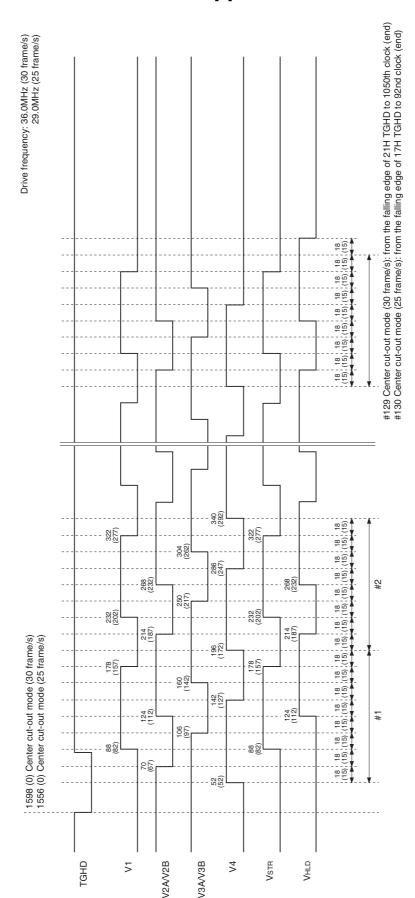
All-pixel Scan Mode (15 frame/s, 12.5 frame/s, 22.5 frame/s)/Center Cut-out Mode (30 frame/s, 25 frame/s)
Horizontal Direction Readout Block [C]



The numbers at the output pulse transition points indicate the count at the rising edge of the clock from the falling edge of TGHD. The numbers on the upper level are for 29.0MHz, and the numbers in parentheses on the lower level are for 29.0MHz.

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Center Cut-out Mode (30 frame/s, 25 frame/s) Horizontal Direction Frame Shift Block [D]



 st SUB pulse generation is prohibited during the frame shift period.

The numbers at the output pulse transition points indicate the count at the rising edge of the clock from the falling edge of TGHD. The numbers on the upper level are for 36.0MHz, and the numbers in parentheses on the lower level are for 29.0MHz.

Notes On Handling

1. Static charge prevention

Image sensors are easily damaged by static discharge. Before handling be sure to take the following protective measures.

- (1) Either handle bare handed or use non-chargeable gloves, clothes or material. Also use conductive shoes.
- (2) Use a wrist strap when handling directly.
- (3) Install grounded conductive mats on the floor and working table to prevent the generation of static electricity.
- (4) Ionized air is recommended for discharge when handling image sensors.
- (5) For the shipment of mounted boards, use boxes treated for the prevention of static charges.

2. Soldering

- (1) Make sure the temperature of the upper surface of the seal glass resin adhesive portion of the package does not exceed 80°C.
- (2) Solder dipping in a mounting furnace causes damage to the glass and other defects. Use a 30W soldering iron with a ground wire and solder each pin in 2 seconds or less. For repairs and remount, cool sufficiently.
- (3) To dismount an image sensor, do not use solder suction equipment. When using an electric desoldering tool, use a thermal controller of the zero-cross On/Off type and connect it to ground.

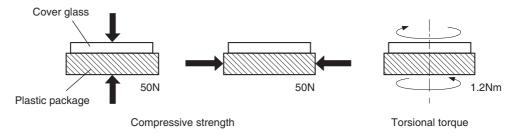
3. Protection from dust and dirt

Image sensors are packed and delivered with care taken to protect the element glass surfaces from harmful dust and dirt. Clean glass surfaces with the following operations as required before use.

- (1) Perform all lens assembly and other work in a clean room (class 1000 or less).
- (2) Do not touch the glass surface with hand and make any object contact with it. If dust or other is stuck to a glass surface, blow it off with an air blower. (For dust stuck through static electricity, ionized air is recommended.)
- (3) Clean with a cotton bud and ethyl alcohol if grease stained. Be careful not to scratch the glass.
- (4) Keep in a dedicated case to protect from dust and dirt. To prevent dew condensation, preheat or precool when moving to a room with great temperature differences.
- (5) When a protective tape is applied before shipping, remove the tape applied for electrostatic protection just before use. Do not reuse the tape.

4. Installing (attaching)

(1) Remain within the following limits when applying a static load to the package. Do not apply any load more than 0.7mm inside the outer perimeter of the glass portion, and do not apply any load or impact to limited portions. (This may cause cracks in the package.)



- (2) If a load is applied to the entire surface by a hard component, bending stress may be generated and the package may fracture, etc., depending on the flatness of the bottom of the package. Therefore, for installation, use either an elastic load, such as a spring plate, or an adhesive.
- (3) The adhesive may cause the marking on the rear surface to disappear, especially in case the regulated voltage value is indicated on the rear surface. Therefore, the adhesive should not be applied to this area, and indicated values should be transferred to the other locations as a precaution.

SONY ICX445ALA

(4) The notch of the package is used for directional index, and that can not be used for reference of fixing. In addition, the cover glass and seal resin may overlap with the notch of the package.

- (5) If the lead bend repeatedly and the metal, etc., clash or rub against the package, dust may be generated by the fragments of resin.
- (6) Acrylate anaerobic adhesives are generally used to attach image sensors. In addition, cyanoacrylate instantaneous adhesives are sometimes used jointly with acrylate anaerobic adhesives to hold the image sensor in place until the adhesive completely hardens. (reference)

5. Others

- (1) Do not expose to strong light (sun rays) for long periods, as color filters will be discolored. When high luminance objects are imaged with the exposure level controlled by the electronic iris, the luminance of the image-plane may become excessive and discoloration of the color filters may be accelerated. In such a case, arrangements such as using an automatic iris with the imaging lens or automatically closing the shutter during power-off are advisable. For continuous use under harsh conditions exceeding the normal conditions of use, consult your Sony representative.
- (2) Exposure to high temperature or humidity will affect the characteristics. Accordingly avoid storage or use in such conditions.
- (3) Brown stains may be seen on the bottom or side of the package. But this does not affect the characteristics.
- (4) This image sensor has sensitivity in the near infrared area. Its focus may not match in the same condition under visible light/near infrared light because of aberration. Incident light component of long wavelength which transmits the silicon substrate may have bad influence upon image.

Package Outline

(Unit: mm)

24pin DIP (UNIT: mm)

24

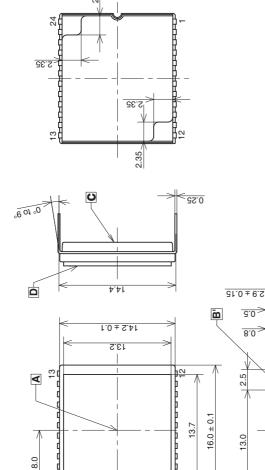
2.5

2.8

2.5

6.0

0.8



"A" is the center of the effective image area.

2. The two points "B" of the package are the horizontal reference. The point "B" of the package is the vertical reference.

⊕ 0.3 M

1.27

8.0 ± 8.5

3. The bottom " \mathbf{C} " of the package, and the top of the cover glass " \mathbf{D} " are the height reference.

4. The center of the effective image area relative to "B" and "B" is (H, V) = $(8.0, 7.1) \pm 0.075$ mm.

5. The rotation angle of the effective image area relative to H and V is $\pm 1^{\circ}$

6. The height from the bottom "C" to the effective image area is 1.41mm \pm 0.1mm. The height from the top of the cover glass "D" to the effective image area is 1.49mm \pm 0.15mm

7. The tilt of the effective image area relative to the bottom "C" is less than 35µm. The tilt of the effective image area relative to the top "D" of the cover glass is less than 50µm.

8. The thickness of the cover glass is 0.5mm, and the refractive index is 1.5.

The notch of the package is used only for directional index, that must not be used for reference of fixing.

Plastic	GOLD PLATING	42 ALLOY	1.20g	AS-A16(E)
PACKAGE MATERIAL	LEAD TREATMENT	LEAD MATERIAL	PACKAGE MASS	DRAWING NUMBER